16:30-16:45  A10 Oral Session A10: Energy Efficiency

Y. H. Cho, S. I. Kim, S. M. Kim, M. K. Kim, O. Seok and M. K. Han, SNU (Korea)

17:31-17:45  A12 Oral Session A12: Microelectronics and Nanotechnology

SSDM 2009 Time Table

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<td>9:40-11:10</td>
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<td>23:45-01:15</td>
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**Friday, October 9**

**Oral Session**

**A-1: SOI/GOI and Channel**

- Self-Excitation of Terahertz Plasma Oscillations in Optically Pumped Graphene
  - V. Ryzhikov, M. Ryzhikov, A. Satou, E. M. Amine and T. Onuki, "Univ. of Aizu, Tohoku Univ. and CREST-JST (Japan)

**A-3: III-V High-Mobility Transistors**

- A. Yamada (Tokyo Tech), "What We Can Expect from Solar Cells"
- Y. Ishida (AIST), "Possibility of Practical Solar Cells? - Dankichi and Sunflower."

**B-4: High-k/Metal Gate I**

- S. Uchida (RCAST, Univ. of Tokyo), "Thin, Light-Weight Flexible Dye Sensitized Solar Cells"
- S. Yoshikawa (Sharp Corp.), "Solar Cells for Mobile Phones"

**B-5: High-k/Metal Gate II**

- H. Hibino, T. Iwai, K. S. Seo, S. Y. Lee, "High-k/Metal Gate I and II"